

**AMENDMENTS TO THE CLAIMS**

1. (Original) A semiconductor light emitter, comprising:

a quantum well active layer which includes nitrogen and at least one other Group-V element; and

barrier layers which are provided alongside said quantum well active layer, wherein said quantum well active layer and said barrier layers together constitute an active layer,

wherein said barrier layers are formed of a Group-III-V mixed-crystal semiconductor that includes nitrogen and at least one other Group-V element, a nitrogen composition thereof being smaller than that of said quantum well active layer.

2. (Original) The semiconductor light emitter as claimed in claim 1, wherein said barrier layers further include phosphorus.

3. (Original) The semiconductor light emitter as claimed in claim 1, wherein said barrier layers are one of GaNAs, GaNPAs, GaInNAs, GaInNPAs, GaNAsSb, GaNPAsSb, GaInNAsSb, and GaInNPAsSb.

4. (Cancelled)

5. (Cancelled)

6. (Original) The semiconductor light emitter as claimed in claim 1, wherein said semiconductor light emitter is a surface emitting semiconductor laser.

7. (Cancelled)

8. (Original) An optical transmission module, comprising the semiconductor light emitter of claim 6 serving as a light source.

9. (Cancelled)

10. (Original) An optical transceiver module, comprising the semiconductor light emitter of claim 6 serving as a light source.

11. (Cancelled)

12. (Original) An optical communication system, comprising the semiconductor light emitter of claim 6 serving as a light source.

13. – 85. (Cancelled)